WEITRON

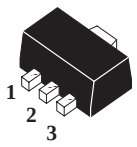
WTMA94

PNP Epitaxial Planar Transistors

Lead(Pb)-Free

*High Voltage

SOT-89



1. BASE
2. COLLECTOR
3. EMITTER

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Rating	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-200	mA
Collector Current - Pulsed	I_{CM}	-300	mA
Collector Power Dissipation	P_D	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

Device Marking

WTMA94=A94

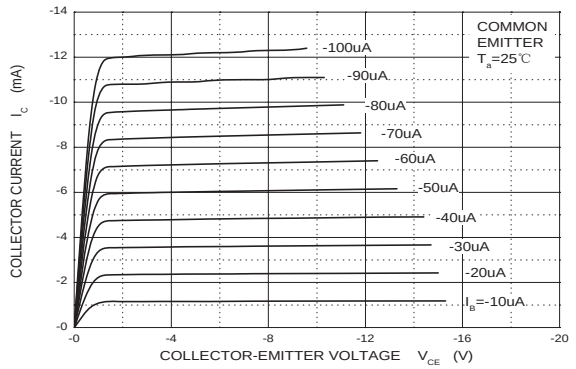
ELECTRICAL CHARACTERISTICS(T_A=25°Cunless otherwise noted)

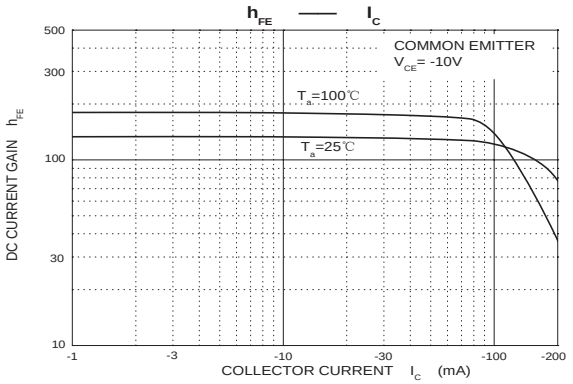
Parameter	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage I_C=-100μA, I_E=0	BV_{CBO}	-400	-	-	V
Collector-Emitter Breakdown Voltage I_C=-1mA, I_B=0	BV_{CEO}	-400	-	-	V
Emitter-Base Breakdown Voltage I_E=-100μA, I_C=0	BV_{EBO}	-5	-	-	V
Collector Cutoff Current V_{CB}=-400V, I_E=0	I_{CBO}	-	-	-0.1	μA
Collector Cut-off Current V_{CE}=-400V, I_B=0	I_{CEO}	-	-	-5	μA
Emitter Cut-off Current V_{EB}=-4V, I_C=0	I_{EBO}	-	-	-0.1	μA

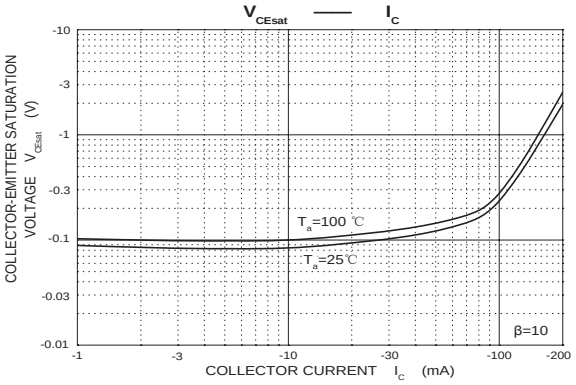
ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

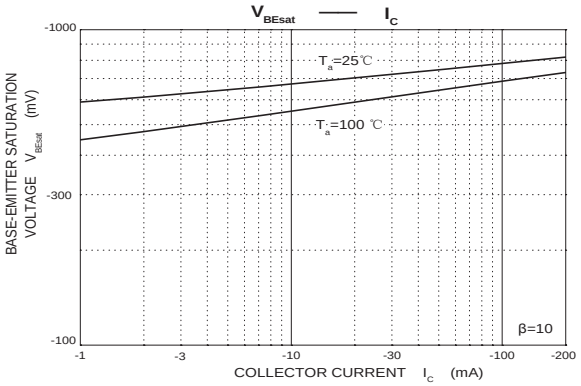
Characteristic	Symbol	Min	Typ	Max	Unit
DC Current Gain					
V_{CE}=-10V, I_C=-10mA	h_{FE1}	80	-	300	-
V_{CE}=-10V, I_C=-1mA	h_{FE2}	70	-	-	
V_{CE}=-10V, I_C=-100mA	h_{FE3}	60	-	-	
V_{CE}=-10V, I_C=-50mA	h_{FE4}	80	-	-	
Collector-Emitter Saturation Voltage					
I_C=-10mA, I_B=-1mA	$V_{CE1(sat)}$			-0.2	V
I_C=-50mA, I_B=-5mA	$V_{CE2(sat)}$			-0.3	
Base-Emitter Saturation Voltage I_C=-10mA, I_B=-1mA	$V_{BE(sat)}$	-	-	-0.75	V
Transition Frequency V_{CE} =-20V, I_C =-10mA, f=30MHz	f_T	50	-	-	MHz

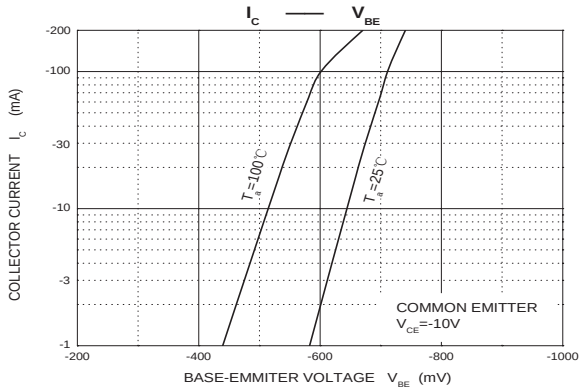
Static Characteristic

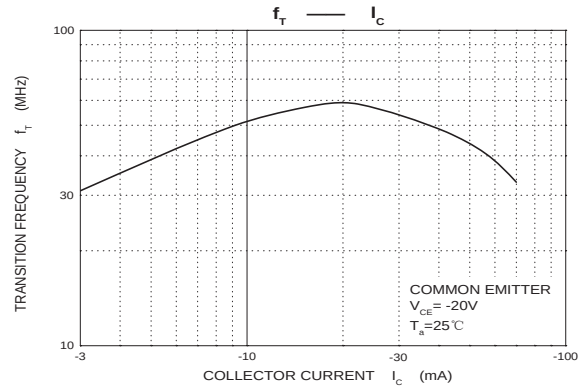


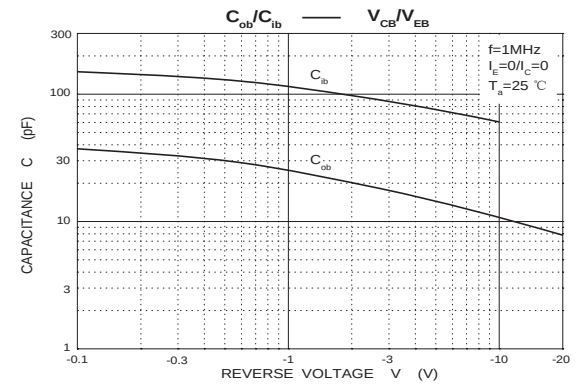


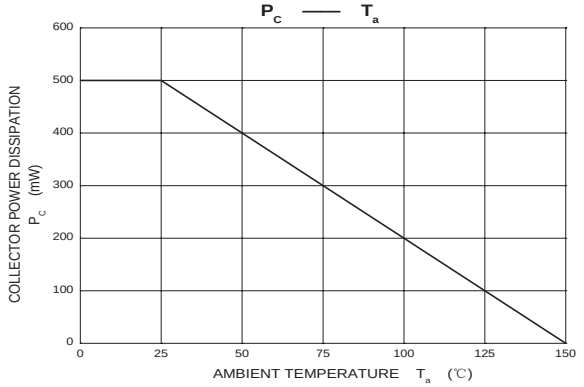






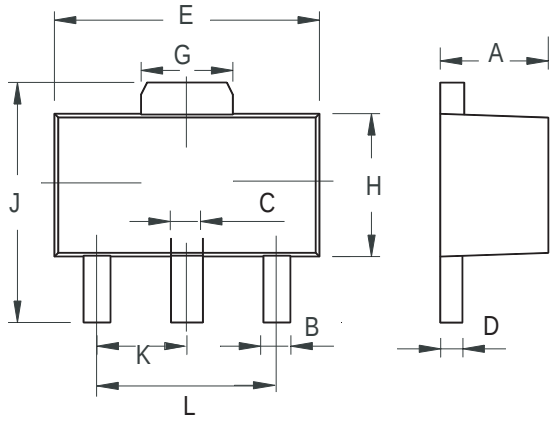






SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	**Min**	**Max**
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100